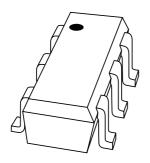
DISCRETE SEMICONDUCTORS

DATA SHEET



BAS70-07SSchottky barrier double diode

Product specification Supersedes data of 1998 Jul 10 2003 Apr 11





Schottky barrier double diode

BAS70-07S

FEATURES

- Low forward voltage
- · Guard ring protected
- · Small SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Blocking diodes.

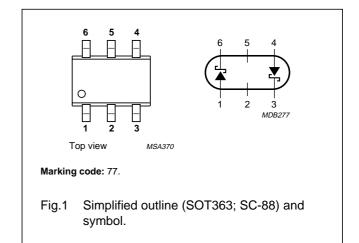
DESCRIPTION

Planar Schottky barrier double diode with an integrated guard ring for stress protection.

Two separate dies are encapsulated in a SOT363 (SC-88) small SMD plastic package.

PINNING

PIN	DESCRIPTION					
1	anode 1					
2	not connected					
3	cathode 2					
4	anode 2					
5	not connected					
6	cathode 1					



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode			•		•
V _R	continuous reverse voltage		_	70	V
I _F	continuous forward current		_	70	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	70	mA
I _{FSM}	non-repetitive peak forward current	$t_p < 10 \text{ ms}$	_	100	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode			•	
V _F	forward voltage	see Fig.2		
		$I_F = 1 \text{ mA}$	410	mV
		I _F = 10 mA	750	mV
		I _F = 15 mA	1	V
I _R	reverse current	V _R = 50 V; note 1; see Fig.3	100	nA
		V _R = 70 V; note 1; see Fig.3	10	μΑ
τ	charge carrier life time (Krakauer method)	I _F = 5 mA	100	ps
C _d	diode capacitance	f = 1 MHz; V _R = 0 V; see Fig.5	2	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	416	K/W

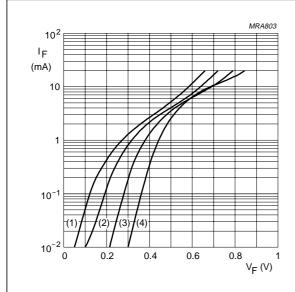
Note

1. Refer to SOT363 standard mounting conditions.

Schottky barrier double diode

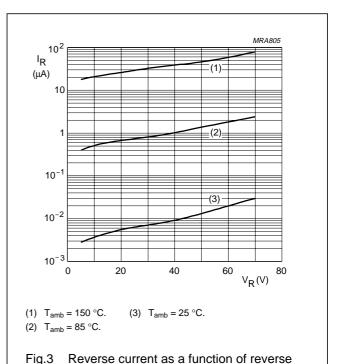
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GRAPHICAL DATA



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



voltage; typical values.

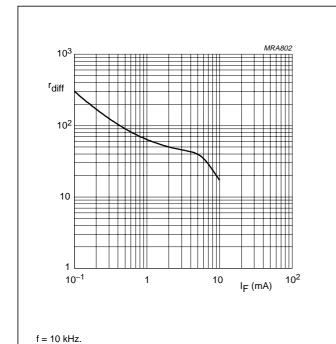
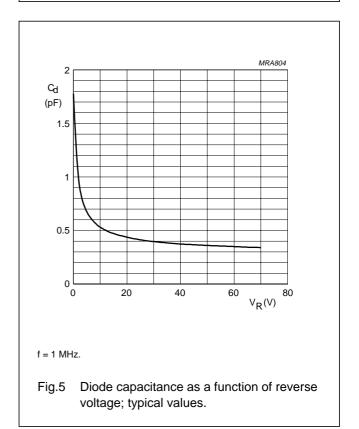


Fig.4 Differential forward resistance as a function of forward current; typical values.



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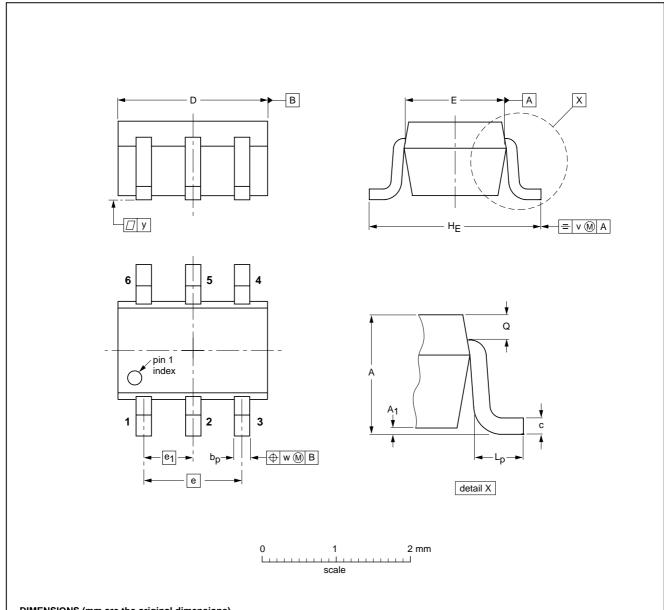
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	٧	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	ENCES	EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT363			SC-88			97-02-28	

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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